IN THE CLAIMS

1. (**Currently Amended**) A method for manufacturing a thin-film magnetic head <u>in a wafer fabrication process</u>, the method comprising the steps of:

sequentially depositing a first magnetic layer, a non-magnetic layer, and a second magnetic layer; and

forming a three-layer pole tip structure located between an air bearing surface and a position at a predetermined height from the air bearing surface by ion milling using no reactive gas said first magnetic layer, said non-magnetic layer, and said second magnetic layer, at the same time and free from using a reactive gas,

said non-magnetic layer being made of a material having an etching rate, for the ion milling using no free from using a reactive gas, equal to or higher than that of a material of said first magnetic layer and said second magnetic layers layer.

- 2. (**Currently Amended**) The method as claimed in claim 1, wherein a material of said non-magnetic layer is one selected from a group of silicon dioxide, tantalum oxide, silicon carbide, and aluminum nitride.
- 3. (**Currently Amended**) The method as claimed in claim 1, wherein a material of said first <u>magnetic layer</u> and <u>said</u> second magnetic <u>layers</u> is nitride containing iron.
- 4. (**Currently Amended**) The method as claimed in claim 1, wherein the material of said non-magnetic layer is tantalum oxide, and wherein the material of said first magnetic layer and said second magnetic layers layer is nickel iron.